

SiC Schottky Barrier Diode

# TRS30H120H

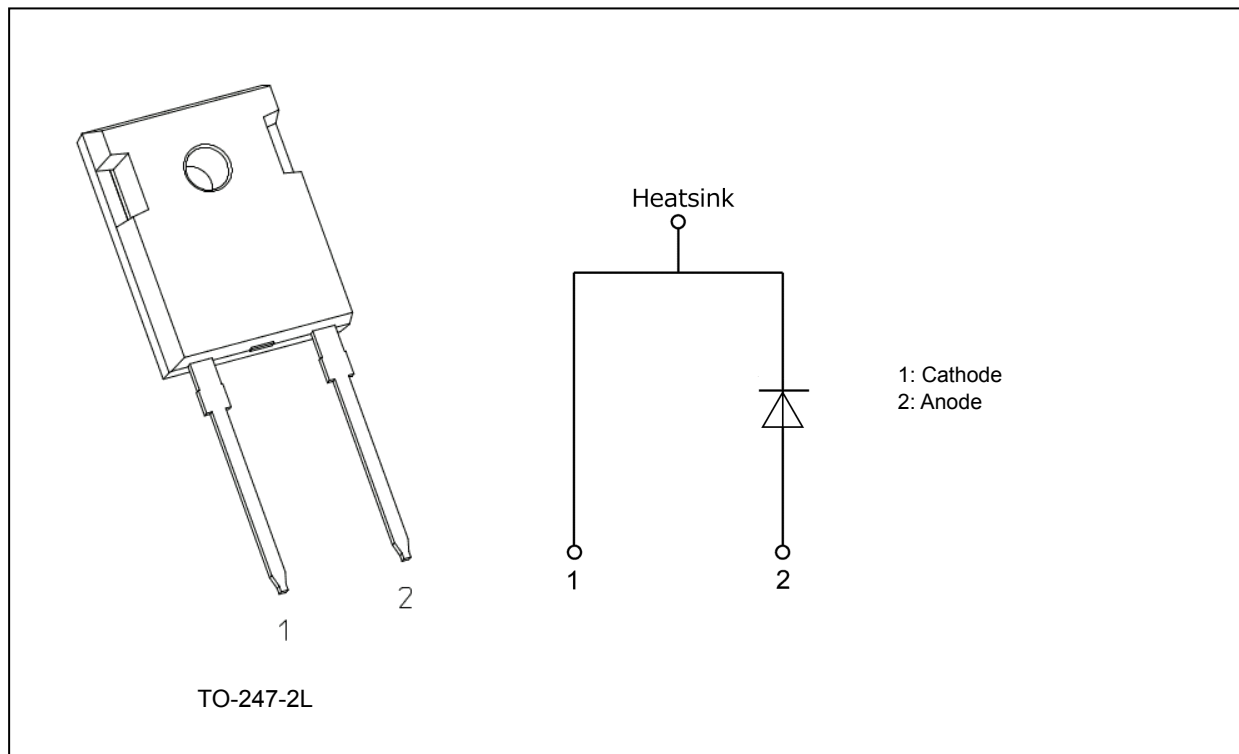
## 1. Applications

- Power Factor Correction
- Solar Inverters
- Uninterruptible Power Supplies
- DC-DC Converters

## 2. Features

- (1) Chip design of 3rd generation
- (2) Low forward voltage :  $V_F = 1.27 \text{ V (typ.)}$
- (3) Low total capacitive charge:  $Q_c = 162 \text{ nC (typ.)}$
- (4) Low reverse current:  $I_R = 2.8 \text{ }\mu\text{A (typ.)}$

## 3. Packaging and Internal Circuit



Start of commercial production  
2024-07

4. Absolute Maximum Ratings (Note) (Unless otherwise specified,  $T_a = 25\text{ }^{\circ}\text{C}$ )

| Characteristics                           | Symbol      | Note    | Rating     | Unit               |
|-------------------------------------------|-------------|---------|------------|--------------------|
| Repetitive peak reverse voltage           | $V_{RRM}$   |         | 1200       | V                  |
| Forward DC current                        | $I_{F(DC)}$ | (Note1) | 30         | A                  |
|                                           |             | (Note2) | 83         |                    |
| Non-repetitive peak forward surge current | $I_{FSM}$   | (Note3) | 210        | A                  |
|                                           |             | (Note4) | 180        |                    |
|                                           |             | (Note5) | 1630       |                    |
| Power dissipation                         | $P_D$       | (Note2) | 394        | W                  |
| Junction temperature                      | $T_j$       |         | 175        | $^{\circ}\text{C}$ |
| Storage temperature                       | $T_{stg}$   |         | -55 to 175 |                    |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note1:  $T_c = 150\text{ }^{\circ}\text{C}$

Note2:  $T_c = 25\text{ }^{\circ}\text{C}$

Note3:  $f = 50\text{ Hz}$  (half-sine wave,  $t = 10\text{ ms}$ ),  $T_c = 25\text{ }^{\circ}\text{C}$

Note4:  $f = 50\text{ Hz}$  (half-sine wave,  $t = 10\text{ ms}$ ),  $T_c = 150\text{ }^{\circ}\text{C}$

Note5: Square wave,  $t = 10\text{ }\mu\text{s}$ ,  $T_c = 25\text{ }^{\circ}\text{C}$

## 5. Thermal Characteristics

| Characteristics                          | Symbol        | Note    | Max  | Unit                 |
|------------------------------------------|---------------|---------|------|----------------------|
| Thermal resistance (junction-to-case)    | $R_{th(j-c)}$ | (Note1) | 0.38 | $^{\circ}\text{C/W}$ |
| Thermal resistance (junction-to-ambient) | $R_{th(j-a)}$ | (Note1) | 50   | $^{\circ}\text{C/W}$ |

Note1:  $T_c = 25\text{ }^{\circ}\text{C}$

6. Electrical Characteristics (Unless otherwise specified,  $T_a = 25\text{ }^{\circ}\text{C}$ )

| Characteristics                     | Symbol | Test Condition                                              | Min | Typ. | Max  | Unit          |
|-------------------------------------|--------|-------------------------------------------------------------|-----|------|------|---------------|
| Forward voltage (pulse measurement) | $V_F$  | $I_F = 15\text{ A}$                                         | —   | 1.0  | —    | V             |
|                                     |        | $I_F = 30\text{ A}$                                         | —   | 1.27 | 1.45 |               |
|                                     |        | $I_F = 30\text{ A}$ , $T_a = 150\text{ }^{\circ}\text{C}$   | —   | 1.64 | —    |               |
| Reverse current (pulse measurement) | $I_R$  | $V_R = 1200\text{ V}$                                       | —   | 2.8  | 180  | $\mu\text{A}$ |
|                                     |        | $V_R = 1200\text{ V}$ , $T_a = 150\text{ }^{\circ}\text{C}$ | —   | 30   | —    |               |
| Total capacitance                   | $C_t$  | $V_R = 1\text{ V}$ , $f = 1\text{ MHz}$                     | —   | 3205 | —    | pF            |
|                                     |        | $V_R = 800\text{ V}$ , $f = 1\text{ MHz}$                   | —   | 107  | —    |               |
|                                     |        | $V_R = 1200\text{ V}$ , $f = 1\text{ MHz}$                  | —   | 104  | —    |               |
| Total capacitive charge             | $Q_C$  | $V_R = 800\text{ V}$ , $f = 1\text{ MHz}$                   | —   | 162  | —    | nC            |

7. Marking

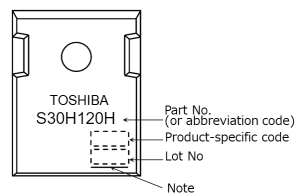


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.  
[[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]  
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.  
The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

| Abbreviation Code | Part Number |
|-------------------|-------------|
| S30H120H          | TRS30H120H  |

8. Usage Considerations

For other design considerations, see the Toshiba website.

9. Characteristics Curves (Note)

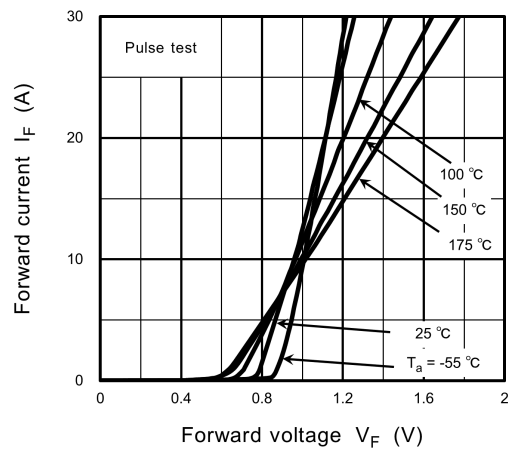


Fig. 9.1  $I_F - V_F$

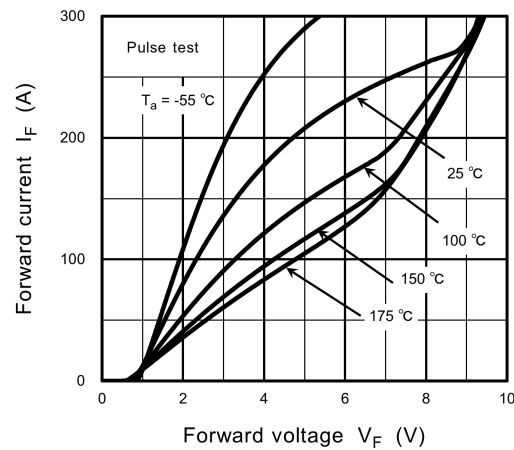


Fig. 9.2  $I_F - V_F$

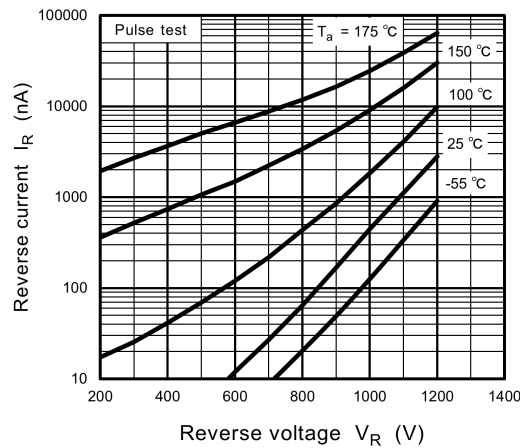


Fig. 9.3  $I_R - V_R$

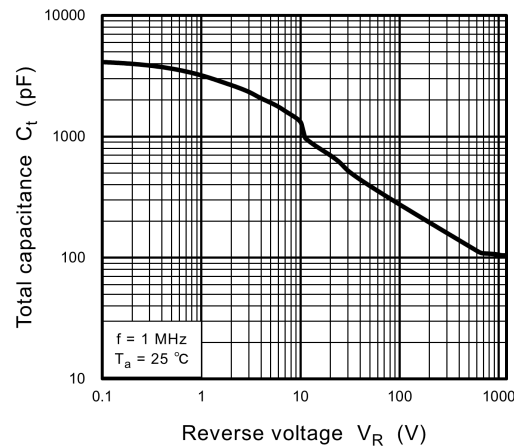


Fig. 9.4  $C_t - V_R$

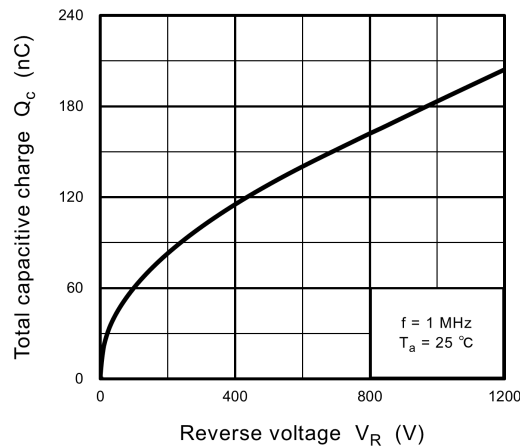


Fig. 9.5  $Q_c - V_R$

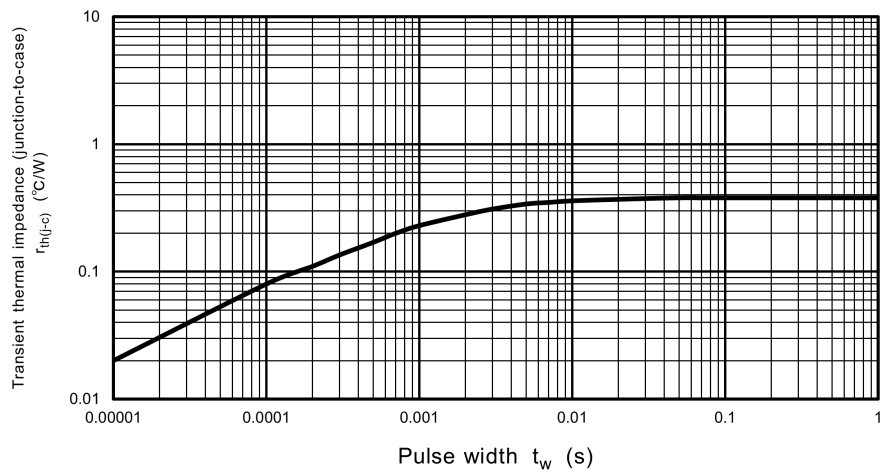


Fig. 9.6  $r_{th(j-c)} - t_w$   
(Guaranteed Maximum)

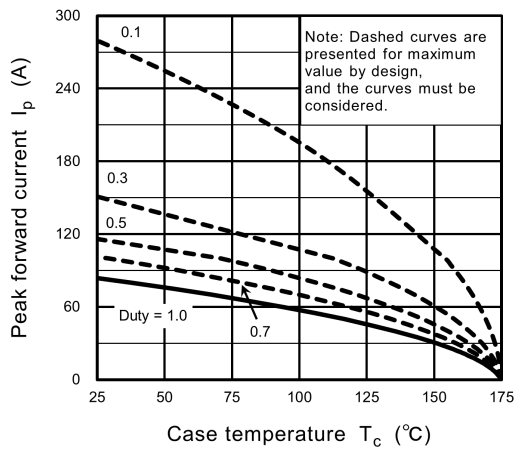


Fig. 9.7  $I_p - T_c$

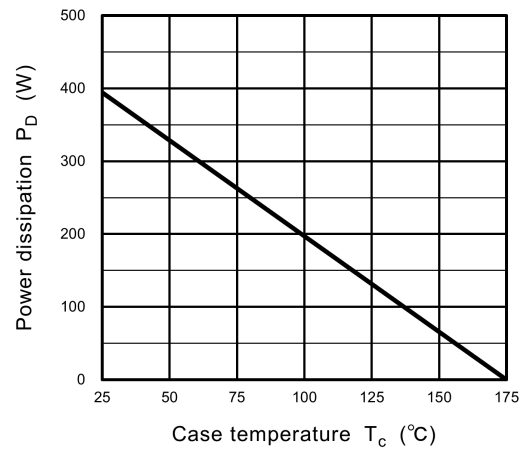
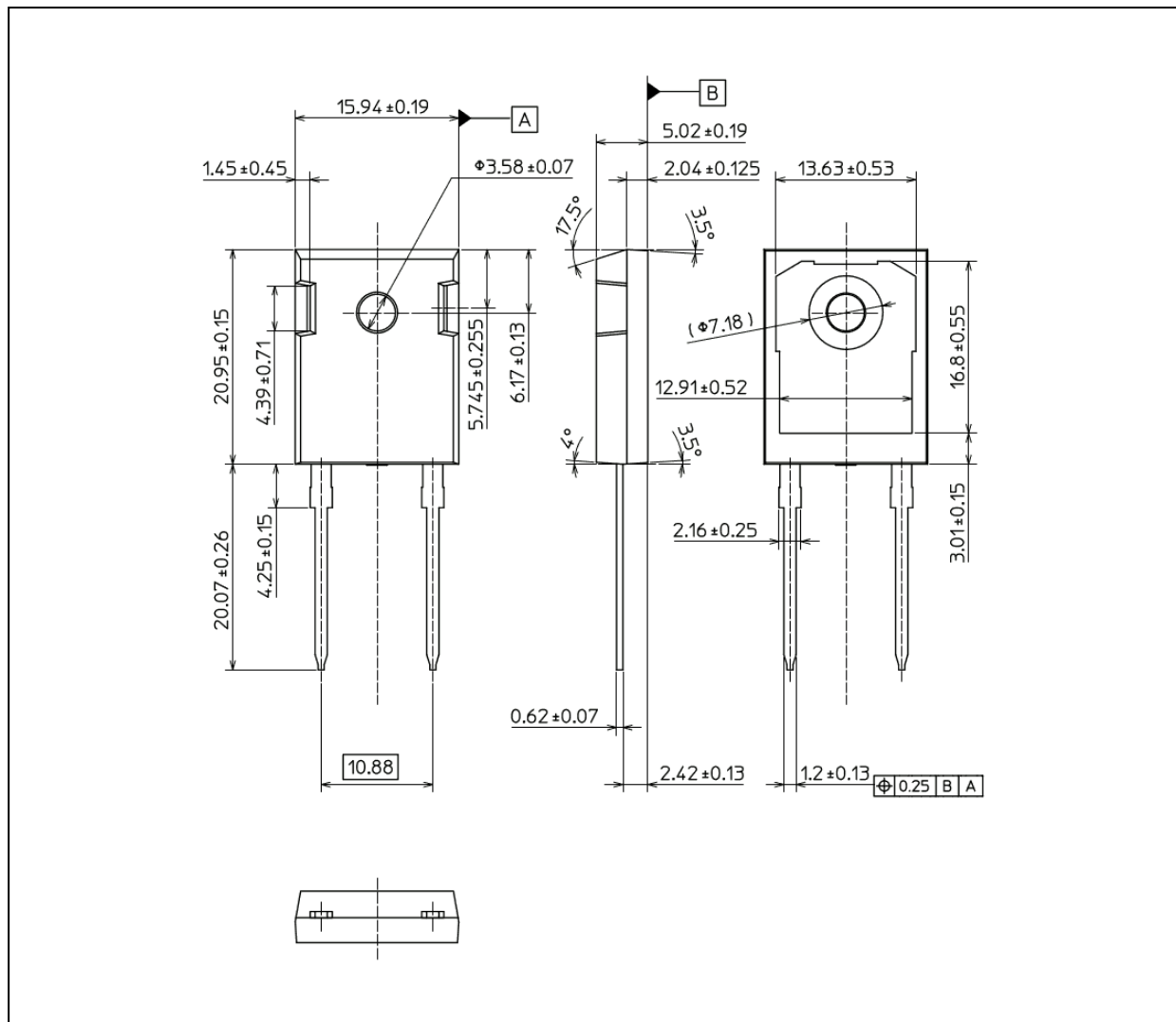


Fig. 9.8  $P_D - T_c$   
(Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

## Package Dimensions

Unit: mm



Weight: 5.98 g (typ.)

| Package Name(s)     |
|---------------------|
| TOSHIBA: 1-16A1A    |
| Nickname: TO-247-2L |

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